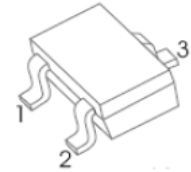


**SOT-323 Plastic-Encapsulate Transistors****BC856W** TRANSISTOR (PNP)**BC857W****BC858W****FEATURES**

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications

**SOT-323**

1. BASE
2. EMITTER
3. COLLECTOR

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
<b>V<sub>CBO</sub></b>	Collector-Base Voltage		
	BC856W	-80	V
	BC857W	-50	
	BC858W	-30	
<b>V<sub>CEO</sub></b>	Collector-Emitter Voltage		
	BC856W	-65	V
	BC857W	-45	
	BC858W	-30	
<b>V<sub>EBO</sub></b>	Emitter-Base Voltage	-5	V
<b>I<sub>c</sub></b>	Collector Current –Continuous	-0.1	A
<b>P<sub>C</sub>*</b>	Collector Power Dissipation	150	mW
<b>T<sub>J</sub></b>	Junction Temperature	150	°C
<b>T<sub>stg</sub></b>	Storage Temperature	-65-150	°C

**DEVICE MARKING**

**BC856AW=3A; BC856BW=3B;**  
**BC857AW=3E; BC857BW=3F;BC857CW=3G;**  
**BC858AW=3J; BC858BW=3K; BC858CW=3L**

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage <b>BC856W</b> <b>BC857W</b> <b>BC858W</b>	V <sub>CBO</sub>	I <sub>C</sub> = -10μA, I <sub>E</sub> =0	-80 -50 -30		V
Collector-emitter breakdown voltage <b>BC856W</b> <b>BC857W</b> <b>BC858W</b>	V <sub>CEO</sub>	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-65 -45 -30		V
Emitter-base breakdown voltage	V <sub>EBO</sub>	I <sub>E</sub> = -1μA, I <sub>C</sub> =0	-5		V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -30 V , I <sub>E</sub> =0		-15	nA
DC current gain <b>BC856AW, 857AW,858AW</b> <b>BC856BW, 857BW,858BW</b> <b>BC857CW,BC858CW</b>	h <sub>FE</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -2mA	125 220 420	250 475 800	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-100mA, I <sub>B</sub> = -5mA		-0.65	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -100mA, I <sub>B</sub> = -5mA		-1.1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -5V, I <sub>C</sub> = -10mA f=100MHz	100		MHz
Collector capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, f=1MHz		4.5	pF

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